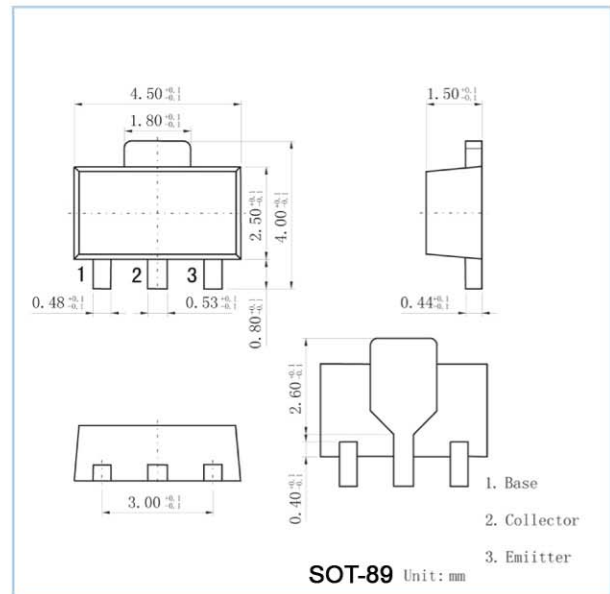


■ Features

- High current (max. 1 A).
- Low voltage (max. 45 V).



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	45	V
Collector-emitter voltage	V_{CE0}	45	V
Emitter-base voltage	V_{EB0}	5	V
Collector current (DC)	I_C	1	A
Peak collector current	I_{CM}	1.5	A
Peak base current	I_{BM}	0.2	A
Power dissipation $T_a \leq 25^\circ\text{C}$ *	P_D	1.3	W
Operating ambient temperature	R_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient *	$R_{th(j-a)}$	94	K/W
Thermal resistance from junction to solder point	$R_{th(j-s)}$	14	K/W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

* Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6 cm².

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	IcBO	V _{CB} = 30 V, I _E = 0			100	nA
		V _{CB} = 30 V, I _E = 0; T _j = 125°C			10	μA
Emitter cutoff current	I _{EBO}	V _{EB} = 5 V, I _C = 0			100	nA
DC current gain	h _{FE}	I _C = 5 mA; V _{CE} = 2 V	40			
		I _C = 150 mA; V _{CE} = 2 V	63		250	
		I _C = 500 mA; V _{CE} = 2 V	25			
DC current gain	h _{FE}	I _C = 150 mA; V _{CE} = 2 V;	BCX55-10	63		160
			BCX55-16	100		250
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA; I _B = 50 mA			0.5	V
Base to emitter voltage	V _{BE}	I _C = 500 mA; V _{CE} = 2 V			1	V
DC current gain ratio of the complementary pairs	$\frac{h_{FE}}{h_{FE}}$	I _C = 150 mA; V _{CE} = 2V		1.3	1.6	
Transition frequency	f _T	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz		130		MHz

■ h_{FE} Classification

TYPE	BCX55	BCX55 -10	BCX55-16
Marking	BE	BG	BM